

## Arrays of Magnetic Nano Particles Using Self-Organised Semiconductor Surfaces

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## Independent Dots

#### Requirement / Goal

- Decrease of size / increase of density
- Stray field (e.g. for memory readout)

#### Handicap

- Super paramagnetic limit ( $E_{anisotropy} < 25 k_B T$ )
- Unavoidable stray field coupling / no independent particles

Possible solution

Large anisotropy to overcome coupling







# SiGe and GaSb

#### SiGe



{105} faceted cross-hatch Si<sub>70</sub>Ge<sub>30</sub>



z-scale: 5 nm

z-scale: 15 nm

z-scale: 20 nm

- Strain relaxation during epitaxial growth and metal evaporation
- Dislocation network
- 4-fold symmetry
- 200 nm periodicity
- Shadow deposition
- Tilted surfaces
- No capping
- Favourable for in-plane magnetisation





- Inhomogeneous ion sputtering of metal / semiconductor heterostructures
- Curvature dependent sputter yield
- 6-fold symmetry
- 50 nm periodicity
- Cut a continuous film.
- Flat discs
- GaSb capping
- Favourable for out-of-plane
  magnetisation





## Imaging of dots (dipolar? coupled)



6.5 ML (1.5 nm) Co shadow
 deposited at 16<sup>o</sup> on Si<sub>0.7</sub> Ge<sub>0.3</sub>

- Co near the top of the SiGe crystallites
- Magnetic contrast in the Co rich regions
- 200 nm x 300 nm wide Co nanomagnets
- Micrometer size domains with correlated magnetization.
- Stronger coupling along the elongation of the nanomagnets. (the dots coalesce?)



## GaSb (roughening $\leftarrow \rightarrow$ smoothing)



#### Three temporal regimes of dot formation dynamic:

- 1. Exponential increase of roughness
- 2. Formation of a roughness maximum
- 3. Roughness Saturation at a lower value. Amplification of a characteristic wavelength, defect reduction with increasing time.

The behaviour is understood from and simulated with the stabilised Kuramoto Sivashinsky (KS) equation





# **Conclusion / Outlook**

- SiGe offers templates applicable for producing nano particles by shadow deposition
  - The coalescence could be cancelled by grazing incident sputtering
- The magnetic structures are stable
- The interaction can be approximated utilising a multipole expansion



- GaSb offers possibility to structure continuous films
- Independent dots (in-plane magnetised)
- Independent dots (out-of plane magnetised) soon.
- Disc size tuneable
- Structure may be improved by large scale pre-patterning



